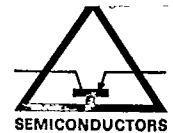


T-27-01

SILICON TRANSISTORS



(g) Power transistors

TYPE NPN PNP	PD Tc=25°C W	VCBO V	VCEO V	VEBO V	IC max A	hFE min	@ max	VCE/IC V	A	VCE (sat) max V	IC/IB @ A/A	fT KHz	ICBO max mA	Case
2N 3055H	117	100	80	7	15	20	70	4	4	1.1	4/0.4	800	5†	TO-3
2N 3055	117	100	60	7	15	20	70	4	4	1.1	4/0.4	800	5†	TO-3
2N 6253	117	55	45	5	15	20	70	4	3	1.0	3/0.3	800	2†	TO-3
2N 6371	117	50	40	5	15	15	60	4	8	4.0	16/4.0	800	2†	TO-3
MJE 3055T	75	70	60	5	10	20	100	4	4	1.1	4/0.4	2*	1	TO-220
SEM NO55	75	50	50	6	10	10	100	4	4	1.0	2/0.1	750	0.2	TO-3
MJE 2955T	75	70	60	5	10	20	70	4	4	1.1	4/0.4	2*	1	TO-220
MJ 2955	115	100	60	7	15	25	70	4	4	3.0	10/3.3	800	5	TO-3
SMC PO55	75	50	50	6	10	10	100	4	4	1.0	2/0.1	750	0.2	TO-3
2N 3773	150	160	140	7	30	15	60	4	8	1.4	8/0.8	800	-	TO-3
2N 3772	150	100	60	7	30	15	60	4	10	1.4	10/1.0	800	-	TO-3
2N 3771	150	50	40	5	30	15	60	4	15	2.0	15/1.5	800	-	TO-3
2N 3442	117	160	140	7	10	20	70	4	3	5.0	10/2.0	-	5†	TO-3
2N 3441	25	160	140	7	3	20	80	4	0.5	1.0	0.5/0.05	-	5†	TO-66
SPD 1404	50	160	140	7	4	20	150	4	3	5.0	10/2.0	-	-	TO-3
2N 3054	25	90	50	7	4	25	150	4	0.5	1.0	0.5/0.05	-	1†	TO-66
2N 6131	50	80	80	5	7	20	100	4	2.5	-	-	-	0.1	TO-220
2N 6130	50	60	60	5	7	20	100	4	2.5	-	-	-	0.1	TO-220
2N 6129	50	40	40	5	7	20	100	4	2.5	-	-	-	0.1	TO-220

Pulse duration $\leq 300 \mu s$; duty cycle $\leq 2\%$ † I_{CEX} ; * MHz

TR10 TR18

Maximum Ratings						Electrical Characteristics at Tj=25°C							Case
TYPE NPN PNP	PD Tc=25°C W	VcBO V	VCEO (sus) V	VEBO V	IC (max) A	IB (max) mA	hFE min/max	@	VCE/IC V/A	fT MHz	ICBO max mA		
2N 5293	36	80	75	7	4	—	30/120		4/0.5	800	—	TO-220	
2N 5294	36	80	75	7	4	—	30/120		4/0.5	800	—	TO-220	
2N 5295	36	60	50	5	4	—	30/120		4/1.0	800	—	TO-220	
2N 5296	36	60	50	5	4	—	30/120		4/1.0	800	—	TO-220	
2N 5297	36	80	70	5	4	—	30/120		4/1.5	800	—	TO-220	
2N 5298	36	80	70	5	4	—	30/120		4/1.5	800	—	TO-220	
2N 6102	40	80	70	5	7	—	30/150		4/2	500	—	TO-220	
2N 6109	40	60	50	5	7	—	30/150		4/2	500	—	TO-220	
2N 6110	40	40	30	5	7	—	30/150		4/2	500	—	TO-220	
2N 6111	40	40	30	5	7	—	30/150		4/2	500	—	TO-220	

FIELD EFFECT TRANSISTORS—N CHANNEL

	Maximum Ratings				Electrical Characteristics at T _J = 25°C								
TYPE	P _D T _a = 25°C W	V _{GS} min V	V _{GD} min V	I _{GSS} max nA	I _{DSS} min; max nA	V _p min; max V	C _{iss} max pF	C _{rss} max pF	Y _{ds} (on) max Ohms	t _{on} max nS	t _{off} max nS	Case	
2N4091	1.8	40	40	0.2 **	30/-	5/10	16	5	30	25	40	TO-18	
2N4092	1.8	40	40	0.2 **	15/-	2/7	16	5	50	35	60	TO-18	
2N4093	1.8	40	40	0.2 **	8/-	1/5	16	5	80	60	80	TO-18	
2N4391	1.8	40	40	0.1	50/100	4/10	14	3.5	30	20	35	TO-18	
2N4392	1.8	40	40	0.1	25/75	2/5	14	3.5	60	20	55	TO-18	
2N4393	1.8	40	40	0.1	5/30	0.5/3	14	3.5	100	20	80	TO-18	
2N4416	0.3*	30	30	0.1	5/15	-/6	4	0.8	-	-	-	TO-72	
2N4416A	0.3*	35	35	0.1	5/15	2.5/6	4	0.8	-	-	-	TO-72	
BFW10	0.3*	30	30	0.1	8/20	-/8	5	0.6 †	-	-	-	TO-72	
BFW11	0.3*	30	30	0.1	4/10	-/6	5	0.6 †	-	-	-	TO-72	
2N3823	0.3*	30	30	0.5	4/20	-/8	6	2	-	-	-	TO-72	

* At Ta = 25°C

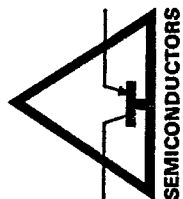
† Typical

** IDGO

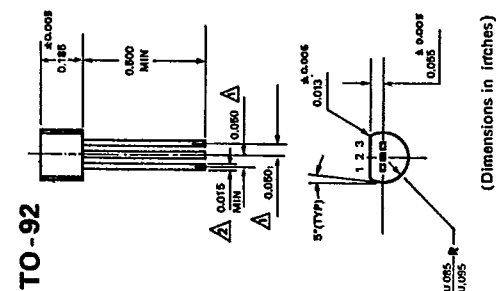
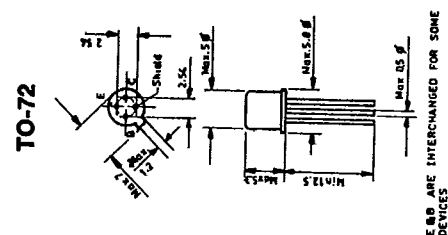
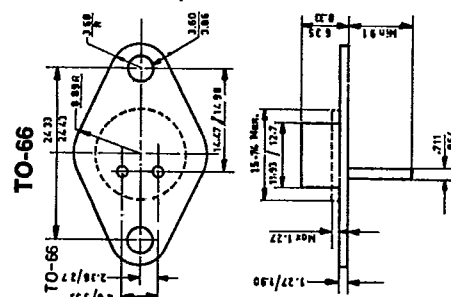
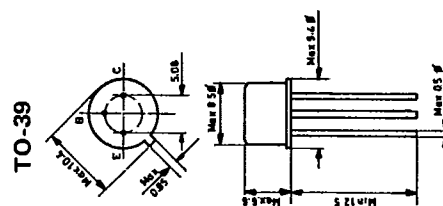
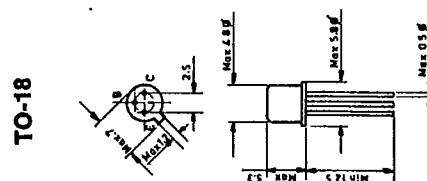
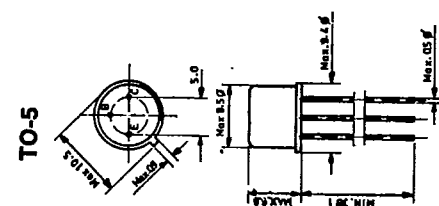
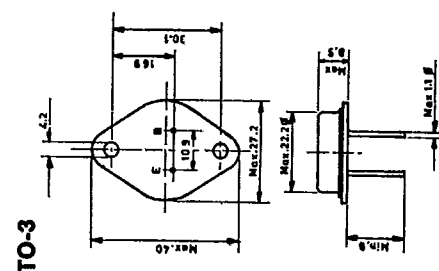
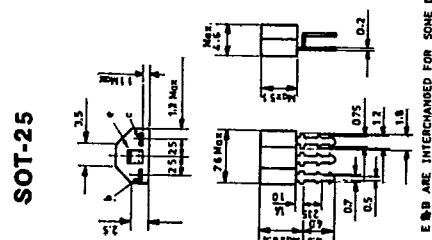
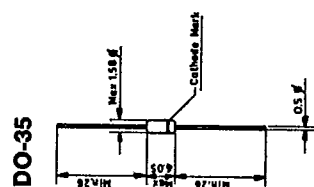
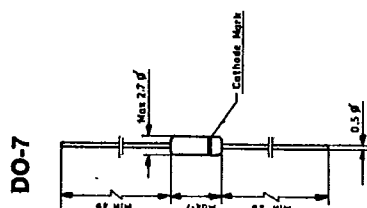
TR 191800

UNIJUNCTION TRANSISTORS

Maximum Ratings					Electrical Characteristics at Tj=25°C							
TYPE	PD Ta=25°C W	IC mA	VB2E V	VB2B1 V	η min/max	RBB min,max K ohms	IP max μA	IV min,max mA	IEB20 max μA	VEB1 sat V	IB2 mod mA	Case
2N2646	0.3	50	30	35	0.56/0.75	4.7/9.1	5	4/-	12	2.0	15	TO-18 mod
2N2647	0.3	50	30	35	0.68/0.82	4.7/9.1	2	8/18	0.2	2.0	15	TO-18 mod



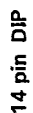
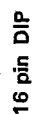
CASE OUTLINES



(Dimensions in inches)

REMB ARE INTERCHANGED FOR SOME
SERVICES

Note : Dimensions in mm unless otherwise specified



Note : Dimensions in mm unless otherwise specified